

SD188SBWS

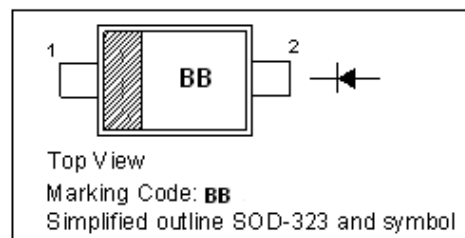
SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

Features

- Small surface mounting type.
- Ultra low V_F . ($V_F=0.38V$ Typ. at 200mA)
- High reliability.

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

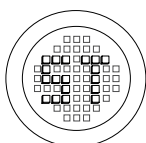


Absolute Maximum Ratings ($T_j = 25^\circ C$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	20	V
DC Reverse Voltage	V_R	10	V
Mean Rectifying Current	I_O	200	mA
Peak Forward Surge Current	I_{FSM}	0.5	A
Storage Temperature Range	T_s	-40 to +125	°C
Junction Temperature Range	T_j	125	°C

Characteristics at $T_j = 25^\circ C$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Forward Voltage	$I_F = 50mA$	V_F	-	-	0.30	V
	$I_F = 200mA$	V_F	-	-	0.41	V
Reverse Current	$V_R = 10V$	I_R	-	-	20	μA



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РАДИОТЕХ

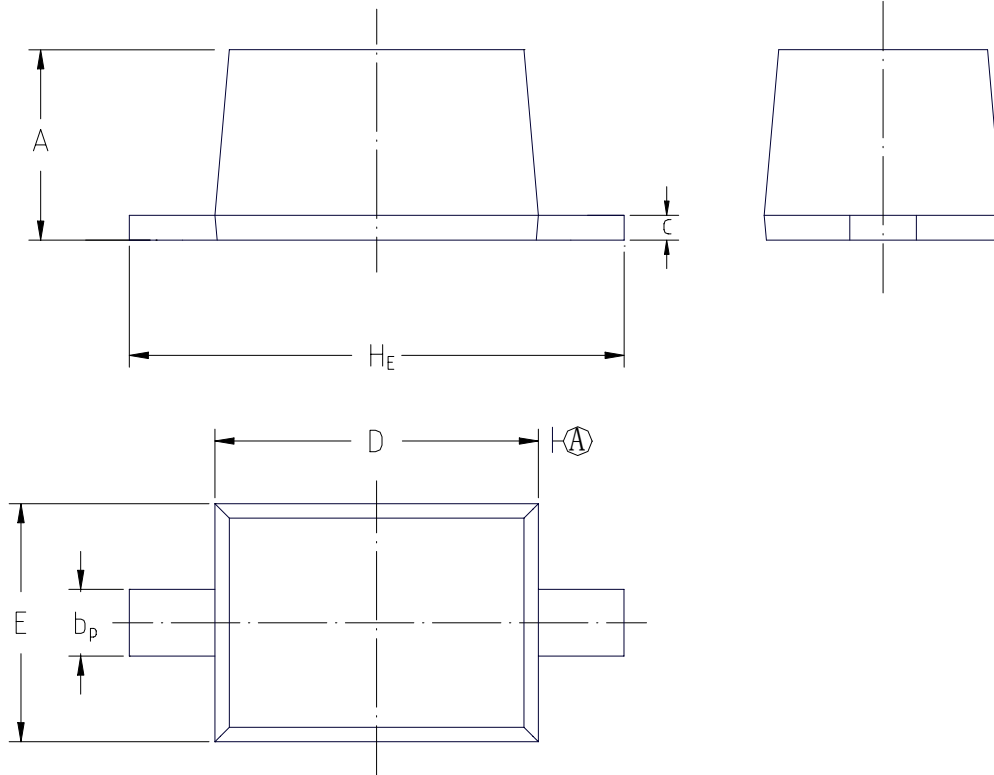
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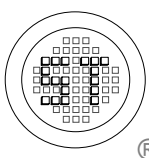
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

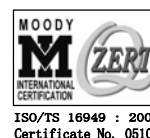


UNIT	A	b_p	c	D	E	H_E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001
Certificate No. 7116



ISO 9001 : 2000
Certificate No. 0200-1000-0000-0000

Dated : 05/05/2005